

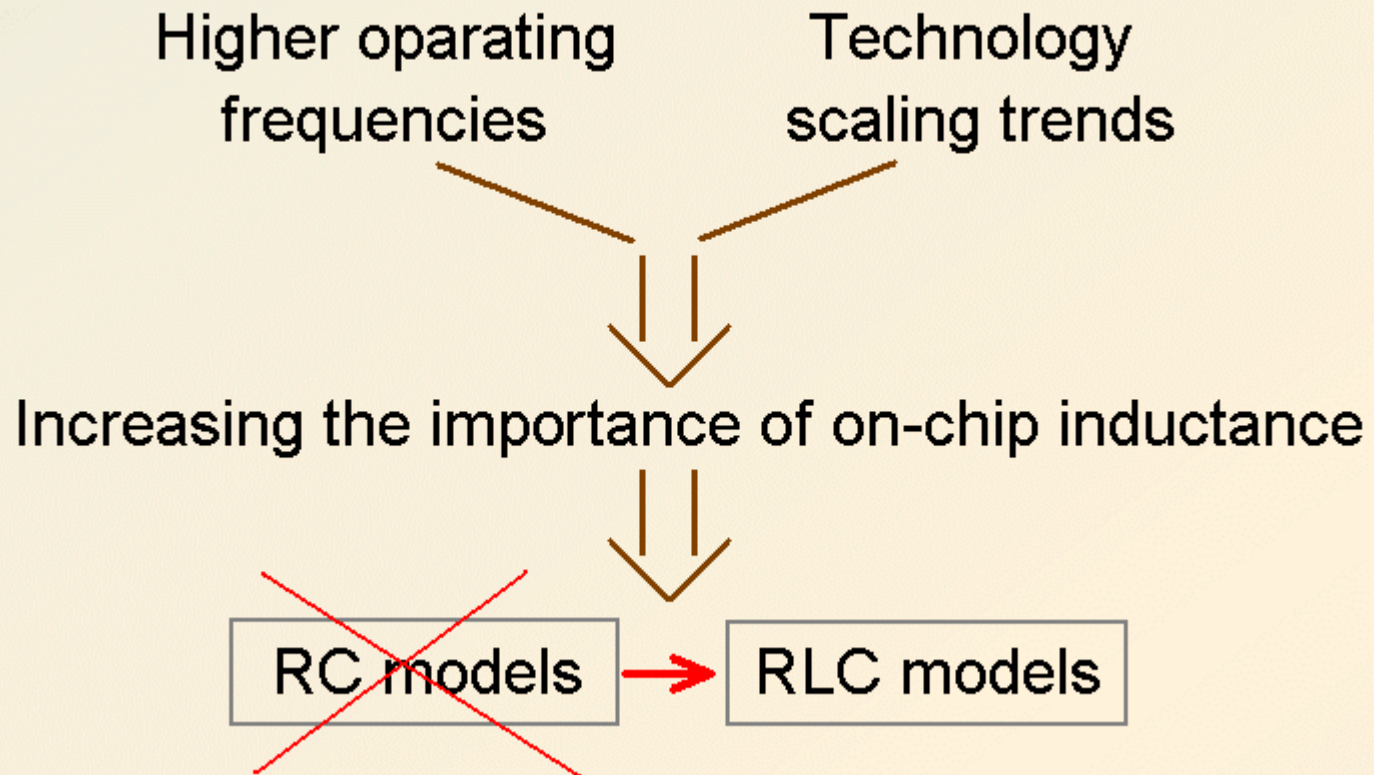
Effect of Inductance on Interconnect Propagation Delay in VLSI Circuits

A. Ligocka, W. Bandurski
Poznan University of Technology,
Poland

Outline

- **Introduction**
- **RLC transmission line model**
- **Short, medium and long lines**
- **Interconnect propagation delay models**
- **Proposed solution**
- **Simulation results**
- **Conclusions**

Introduction (1)



Introduction (2)

RC → RLC model conditions [2]

$$C_L \ll Cd$$

$$\frac{Rd}{2Z_0} \leq 1$$

$$Z_{DRV} < nZ_0$$

$$n = 0.5 \div 1$$

Short, medium and long lines

- Short lines

$$R > 500 \frac{\Omega}{cm}$$

$$l \approx \lambda \Leftrightarrow d\sqrt{LC} \approx T_r$$

- Medium lines

$$R < 500 \frac{\Omega}{cm}$$

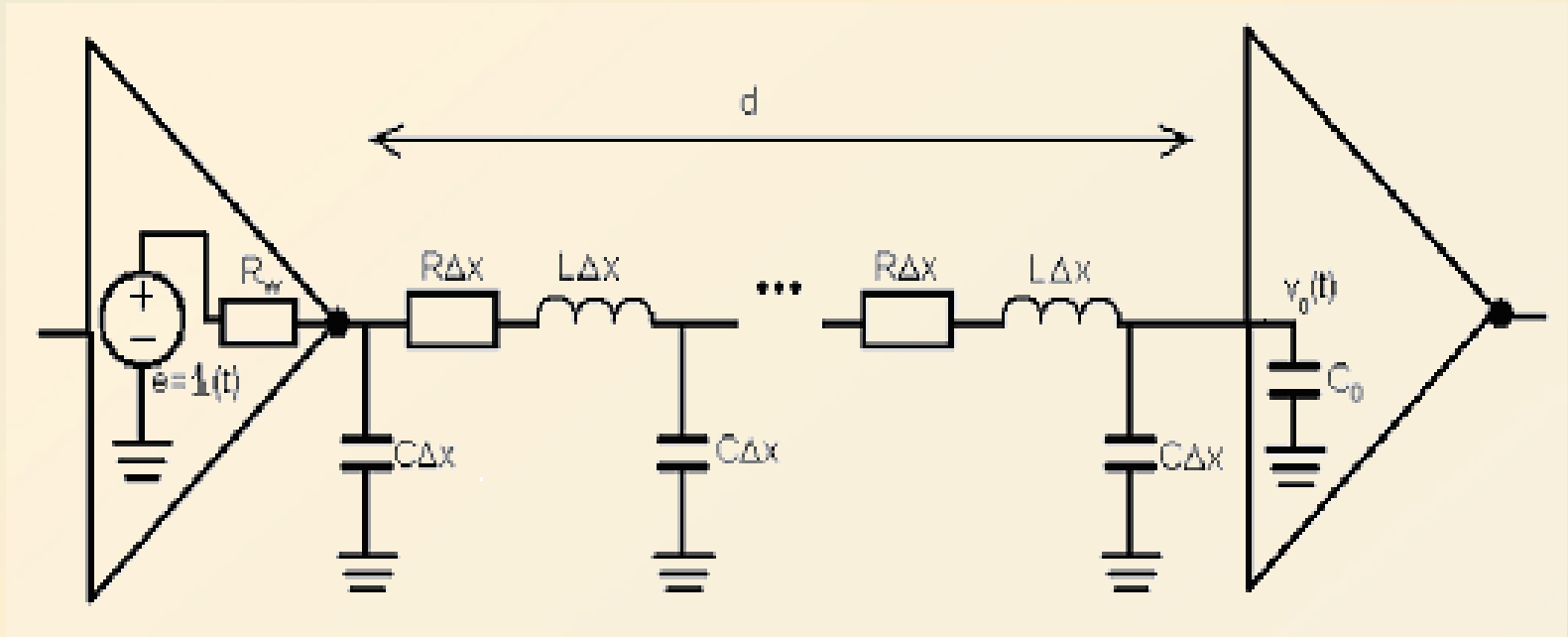
$$l < \lambda \Leftrightarrow d\sqrt{LC} < T_r$$

- Long lines

$$R < 100 \frac{\Omega}{cm}$$

$$l \approx \lambda \Leftrightarrow d\sqrt{LC} \approx T_r$$

RLC transmission line model



Interconnect propagation delay models

- **Ismail-Friedman**

$$T_{50\%} = \frac{e^{-2.9\zeta^{1.35}} + 1.48\zeta}{\omega_n}$$

$$\zeta = \zeta_{line} \frac{R_T + C_T + R_T C_T + 0.5}{\sqrt{1 + C_T}}$$

$$\zeta_{line} = \frac{R_t}{2} \sqrt{\frac{C_t}{L_t}}, \quad R_T = \frac{R_w}{R_t}, \quad C_T = \frac{C_0}{C_t}, \quad \omega_n = \frac{1}{\sqrt{L_t(C_t + C_0)}},$$

for $0 < C_T < 1, \quad 0 < R_T < 1$

R_t, L_t, C_t – total resistance, inductance and capacitance of transmission line ($R_t = R_d$ where d -line length, etc.).

Proposed solution (1)

Exact formula for voltage across Co (1)

$$U_2(s) = H(s) \frac{1}{s}$$

$$H(s) = \frac{Z_c(s)}{Z_c(s) + R_w} \frac{(1 + \rho_o(s)) \exp(-\gamma(s)d)}{1 - \rho_o(s)\rho_w(s) \exp(-2\gamma(s)d)}$$

$\rho_w(s)$, $\rho_o(s)$ – input and output reflection coefficients respectively,
 $Z_c(s)$ – characteristic impedance of the line,
 $\gamma(s)$ - propagation coefficient,
 d – length of the line

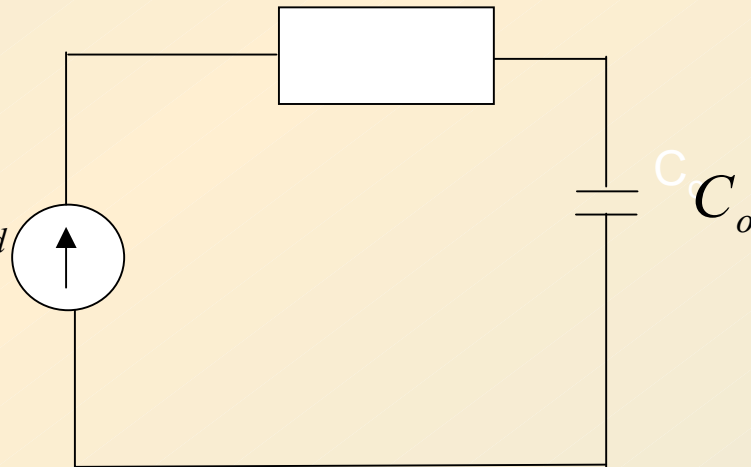
$$H_0(s) = \frac{Z_c(s)}{Z_c(s) + R_w} (1 + \rho_o(s)) \exp(-\gamma(s)d) \quad 0 \leq t < 3T$$

Proposed solution (1b)

C

$$Z_c(s) = Z_o \sqrt{1 + \frac{R}{sL}}$$

$$E_w(s) = \frac{2E_o}{s} \frac{Z_c(s)}{Z_c(s) + R_w} e^{-\gamma(s)d}$$



Proposed solution (2)

Exact formula for voltage across Co (2)

$$U_{20}(p) = \frac{2e^{\frac{-p}{\sqrt{1+C_T}}} \exp\left(-\frac{p}{\sqrt{1+C_T}}(F(p)-1)\right)}{p \left[1 + p \frac{2R_T C_T \zeta_{line}}{\sqrt{1+C_T}} + pF(p) \frac{C_T}{\sqrt{1+C_T}} + \frac{2R_T \zeta_{line}}{F(p)} \right]}$$

where

$$F(p) = \sqrt{1 + \frac{2\zeta_{line} \sqrt{1+C_T}}{p}}, \quad p = \frac{s}{\omega_n}$$

Proposed solution (3)

Approximation of the voltage across Co

$$U_{2a}(p) = e^{\frac{-p}{\sqrt{1+C_T}}} \left[a_0 + a_1 \frac{1}{p} + a_2 \frac{1}{p^2} + a_3 \frac{1}{p^3} \dots \right]$$

where

$$a_n = \frac{1}{n!} \left. \frac{d^n U_{2a}(z)}{dz^n} \right|_{z=0} \quad z = \frac{1}{p}.$$

Proposed solution (4)

Approximation coefficients

$$a_0 = a_1 = 0$$

$$a_3 = a_2 \left[\frac{1}{2} \zeta_{line}^2 - \frac{((2R_T + C_T)\zeta_{line} + 1)}{(2R_T\zeta_{line} + 1)C_T} \right] \quad a_2 = \frac{\exp(-\zeta_{line})\sqrt{1+C_T}}{2R_T C_T \zeta_{line} + C_T}$$

$$a_4 = a_2 \left[\frac{1}{2} \zeta_{line}^3 \left(\left(\frac{1}{4} \zeta_{line} - 1 \right) (1 + C_T) \right) - \frac{\zeta_{line}^2 (1 + C_T)}{(2R_T\zeta_{line} + 1)C_T} \left(\frac{C_T}{2} + 2R_T \right) + \right. \\ \left. (1 + C_T) \left(\frac{2R_T C_T \zeta_{line}^2 + C_T \zeta_{line}}{-2 - 2C_T \zeta_{line} - 4R_T} \right) \cdot \frac{\zeta_{line} (1 + \zeta_{line} (C_T + R_T))}{2C_T^2 (2R_T \zeta_{line} + 1)^2} \right]$$

Proposed solution (5)

Approximate formula for voltage across Co (3)

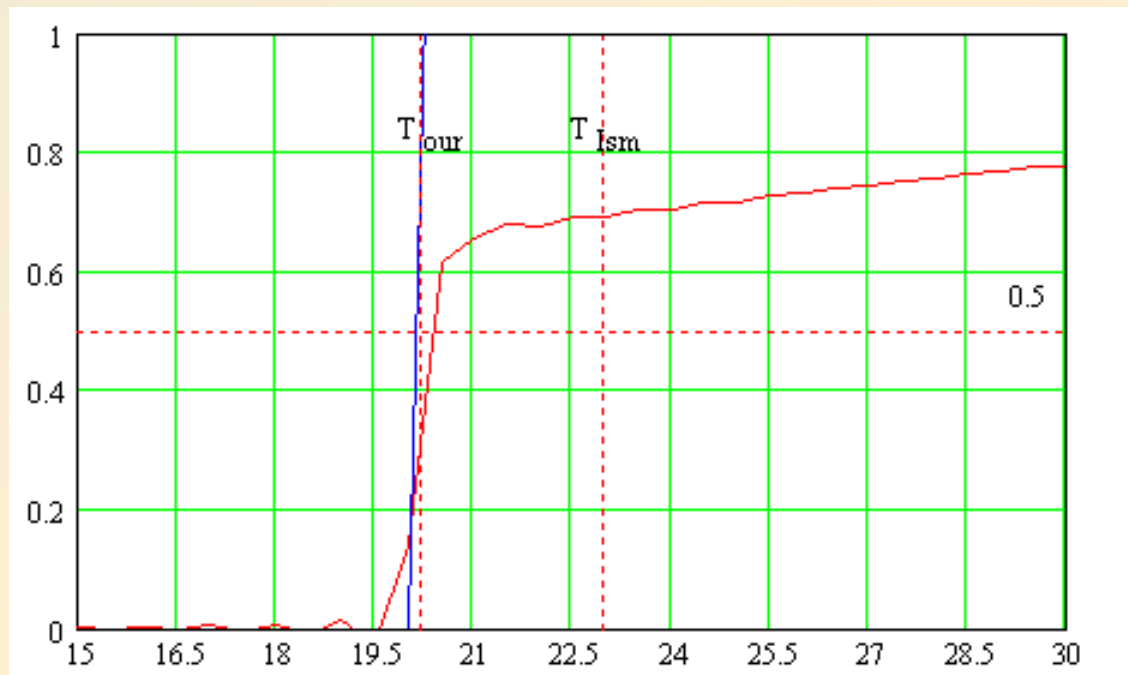
$$u_{2a}(\tau) = 2 \left[a_2 \left(\tau - \frac{1}{\sqrt{1+C_T}} \right) + \frac{a_3}{2} \left(\tau - \frac{1}{\sqrt{1+C_T}} \right)^2 + \frac{a_3}{6} \left(\tau - \frac{1}{\sqrt{1+C_T}} \right)^3 + \dots \right]$$

$$u_{2a}(T_{our}) = \frac{1}{2}$$

$$\tau = t\omega_n$$

Simulation results (1)

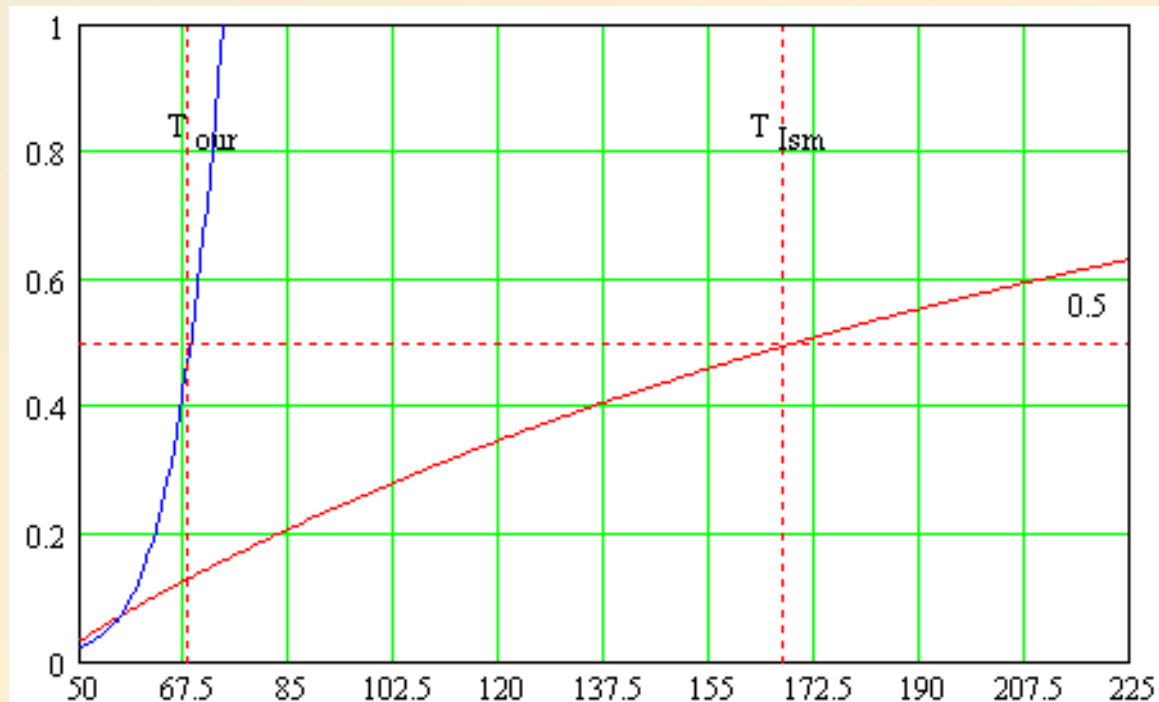
Ismail-Friedman method examination



Parameters: $R=100[\text{Ohm}]$, $L=1.6[\text{nH/cm}]$, $C=1[\text{pF/cm}]$, $Z_{drv}=25[\text{Ohm}]$ $d=0.5[\text{cm}]$,
($C_T=0.01$, $R_T=0.5 \Rightarrow C_0=0.01\text{pF}$); data taken from [2]

Simulation results (1)

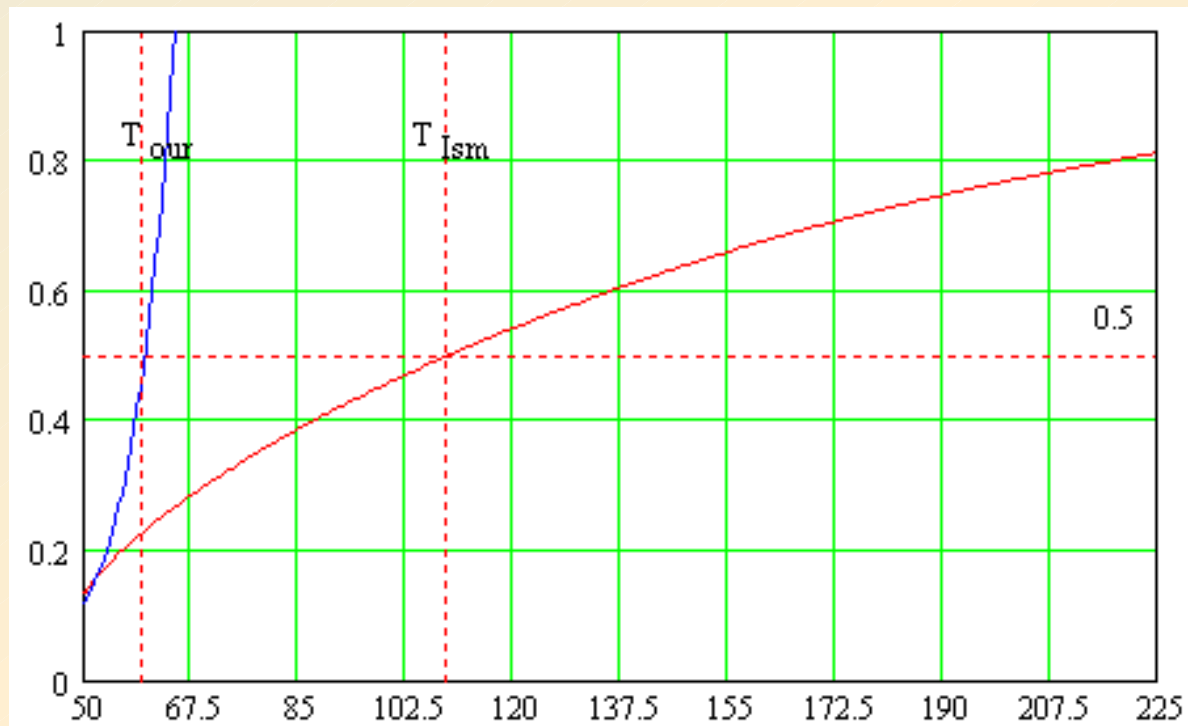
Short lines



Parameters: $R=494[\text{Ohm}]$, $L=4.75[\text{nH/cm}]$, $C=1.73[\text{pF/cm}]$, $Z_{drv}=50[\text{Ohm}]$
 $d=0.5[\text{cm}]$, data taken from [1]

Simulations results (2)

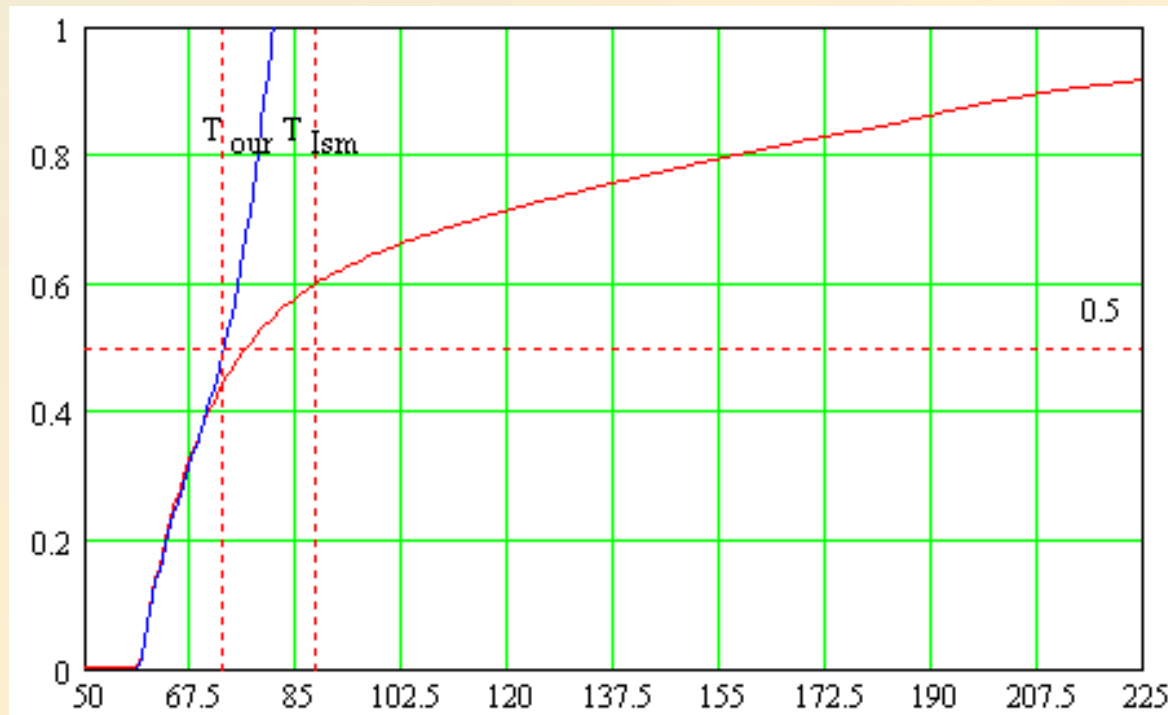
Medium lines



Parameters: $R=248[\text{Ohm}]$, $L=3.7[\text{nH/cm}]$, $C=1.85[\text{pF/cm}]$, $Z_{drv}=50[\text{Ohm}]$,
 $d=0.5[\text{cm}]$, data taken from [1]

Simulations results (3)

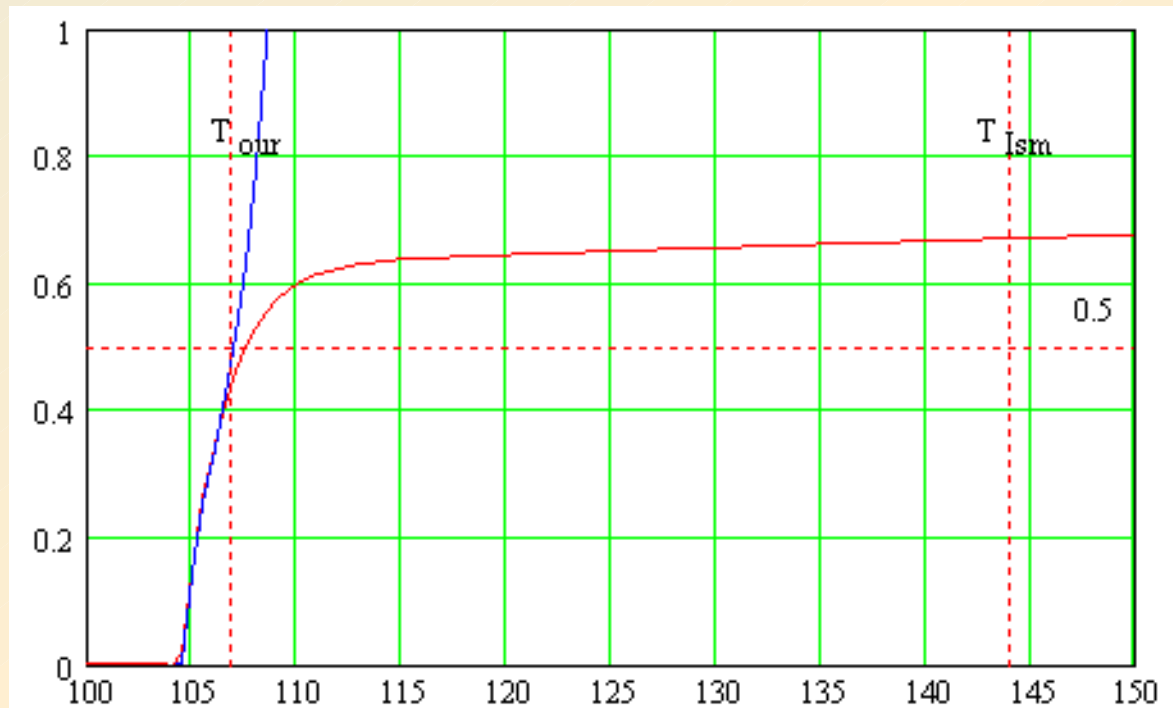
Long lines (1)



Parameters: $R=76[\text{Ohm}]$, $L=5.3[\text{nH/cm}]$, $C=2.6[\text{pF/cm}]$, $Z_{drv}=50[\text{Ohm}]$, $d=0.5[\text{cm}]$, data taken from [1]

Simulations results (1)

Long lines (2)



Parameters: $R=8[\text{Ohm}]$, $L=1.6[\text{nH/cm}]$, $C=27.3[\text{pF/cm}]$, $Z_{drv}=11[\text{Ohm}]$,
 $d=0.5[\text{cm}]$, data taken from [1]

Conclusions

- Moments of the voltage step response can be calculated in analytical way relatively easy
- The closed-form Ismail formula for propagation delay gives inaccurate results in some cases (long lines)
- Our approach gives better results for long lines.
- The accuracy of our approach can be increased by taking more terms in series

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